

In the Specification

**Please delete paragraph 0025, and replace it with the following paragraph:**

[0025] Fig. 5 is a cross sectional view showing the step of stripping the sacrificial oxide of Fig. 4 in the support area only using a block mask 80 that entirely covers only the array area 102.

**Please delete paragraph 0038, and replace it with the following paragraph:**

[0038] Referring to Fig. 4, the pad oxide layer 22 is then stripped from both the array areas 102 and the support areas 104 on substrate 10. Preferably, the pad oxide layer 22 is stripped using a wet etch technique. A sacrificial oxide layer 70 is then grown over all exposed surface areas of the DRAM, in both array and support areas, for the array and the support implants. However in the preferred embodiment, wherein the isolation trenches 30 comprise oxide, grown oxide will not form over the oxide isolation trenches 30 as shown in Fig. 4.

*Please enter 37 CFR 1.312 amendment  
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*D.C.  
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